L	Hits	Search Text	DB	Time stamp
Number	210	(giran iliana arabida) gama (ngatulana	USPAT;	2004/03/02
1	312	(Sic or silicon carbide) same (acetylene or "c.sub.2H.sub.4") same (silane)	US-PGPUB;	14:47
		or "C.Sub.2H.Sub.4") Same (Silane)	EPO; JPO;	14.4/
			DERWENT;	
			IBM TDB	
2	130	(Sic or silicon carbide) same (acetylene	USPAT;	2004/03/02
4	130	or "c.sub.2H.sub.4") near10 (silane)	US-PGPUB;	14:47
		Of C.Sub.211.Sub.4 ) Hear to (Straine)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
3	60	(Sic or silicon carbide) near10	USPAT;	2004/03/02
		(acetylene or "c.sub.2H.sub.4") near10	US-PGPUB;	14:48
		(silane)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	19		USPAT;	2004/03/02
		(acetylene or "c.sub.2H.sub.4") near10	US-PGPUB;	15:45
		(silane)	EPO; JPO;	
			DERWENT;	
_		H1160306H	IBM_TDB	2004/02/02
5	11	"1162326"	USPAT;	2004/03/02 15:45
			US-PGPUB; EPO; JPO;	10:40
			DERWENT;	
			IBM TDB	1
6	4	"01162326"	USPAT;	2004/03/02
0	,	01102320	US-PGPUB;	16:16
			EPO; JPO;	
			DERWENT;	
		,	IBM_TDB	
7	178	(kuniaki near2 yagi or hiroyuki near2	USPAT;	2004/03/02
		nagasawa).in.	US-PGPUB;	16:16
			EPO; JPO;	
	-		DERWENT;	
		l	IBM_TDB	
8	43	((kuniaki near2 yagi or hiroyuki near2	USPAT;	2004/03/02 16:17
		nagasawa).in.) and (sic or silicon adj	US-PGPUB;	16:17
		carbide)	EPO; JPO; DERWENT;	
			IBM TDB	
1_	674	(sic or silicon adj carbide) same surface	USPAT;	2004/02/24
	0,1	near2 react\$4	US-PGPUB;	10:32
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	539		USPAT;	2004/02/24
		surface near2 react\$4	US-PGPUB;	10:32
1			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	2004/02/24
-	115		USPAT;	2004/02/24
		surface near2 react\$4) same (si or   silicon adj substrate)	US-PGPUB; EPO; JPO;	10:24
		stricon and substrace;	DERWENT;	]
			IBM TDB	
_	45	((sic or silicon adj carbide) near10	USPAT;	2004/02/24
	3	surface near2 react\$4) near10 (sic or	US-PGPUB;	11:09
		silicon adj carbide) near4 (layer or	EPO; JPO;	
		film) same (si or silicon adj substrate)	DERWENT;	
			IBM_TDB	
-	1169		USPĀT;	2004/02/24
1		or film) and temperature near4 rate	US-PGPUB;	11:10
			EPO; JPO;	
			DERWENT;	
		[, ,	IBM_TDB	2004/02/24
-	135		USPAT;	2004/02/24
		or film) same (heat\$3 or temperature)	US-PGPUB;	11:11
		near4 rate	EPO; JPO; DERWENT;	
	*		IBM TDB	
L	L		םמד זיםד	I

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_	5	(sic or silicon adj carbide) near4 (layer or film) same (heat\$3 or temperature)	USPAT; US-PGPUB;	2004/02/24
		near4 rate same rapid	EPO; JPO; DERWENT;	
			IBM_TDB	
-	191	(sic or silicon adj carbide) near4 (layer or film) and (heat\$3 or temperature)	USPAT; US-PGPUB;	2004/02/24
		near4 rate near10 grow\$5	EPO; JPO;	11.50
		grant and manager grants	DERWENT;	
			IBM_TDB	
-	31	(sic or silicon adj carbide) near4 (layer or film) and (heat\$3 or temperature)	USPAT; US-PGPUB;	2004/02/24
		near4 rate near10 grow\$5 same (sic or	EPO; JPO;	, 11.50
		silicon adj carbide)	DERWENT;	
		(-1	IBM_TDB	2004/02/24
-	223	(sic or silicon adj carbide) near4 (layer or film) and (heat\$3 or temperature)	USPAT; US-PGPUB;	2004/02/24
		near2 rate same (sic or silicon adj	EPO; JPO;	11.03
		carbide)	DERWENT;	
	8	(sic or silicon adj carbide) near4 (layer	IBM_TDB USPAT;	2004/02/24
-	,	or film) and (heat\$3 or temperature)	US-PGPUB;	11:40
		near2 rate same growth near2 temperature	EPO; JPO;	
		same (sic or silicon adj carbide)	DERWENT;	
_	12	(sic or silicon adj carbide) near4 (layer	IBM_TDB USPAT;	2004/02/24
		or film) and (heat\$3 or temperature)	US-PGPUB;	11:44
		near2 rate near5 (ramp\$4 or elevat\$4)	EPO; JPO;	
		same (sic or silicon adj carbide)	DERWENT; IBM TDB	
-	39	(heat\$3 or temperature) near2 rate near5	USPAT;	2004/02/24
		(ramp\$4 or elevat\$4) same (sic or silicon	US-PGPUB;	11:46
		adj carbide)	EPO; JPO;	
			DERWENT; IBM TDB	
-	27		USPAT;	2004/02/24
		(ramp\$4 or elevat\$4) same (sic or silicon	US-PGPUB;	11:44
		adj carbide)) not ((sic or silicon adj carbide) near4 (layer or film) and	EPO; JPO; DERWENT;	
		(heat\$3 or temperature) near2 rate near5	IBM_TDB	
		(ramp\$4 or elevat\$4) same (sic or silicon		
_	61	adj carbide)) (heat\$3) near2 rate same growth near2	USPAT;	2004/02/24
		temperature	US-PGPUB;	11:46
			EPO; JPO;	
			DERWENT; IBM TDB	
-	7	(heat\$3) near2 rate same growth near2	USPAT;	2004/02/24
		temperature same (sic or silicon adj	US-PGPUB;	11:47
		carbide)	EPO; JPO; DERWENT;	
			IBM TDB	
-	474	(heat\$3) near2 rate same (sic or silicon	USPAT;	2004/02/24
		adj carbide)	US-PGPUB;	11:47
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	34	(heat\$3) near2 rate same (sic or silicon	USPAT;	2004/02/24
		adj carbide) near3 (film or layer)	US-PGPUB; EPO; JPO;	11:53
			DERWENT;	
_	20	#150# popp5 pato same /sis 1-	IBM_TDB	2004/02/24
	29	"150" near5 rate same (sic or silicon adj carbide) near3 (film or layer)	USPAT; US-PGPUB;	2004/02/24 11:55
		-, (	EPO; JPO;	
,			DERWENT;	
_	215	(\$3minute or \$3min) near5 rate same (sic	<pre>IBM_TDB USPAT;</pre>	2004/02/24
		or silicon adj carbide) near3 (film or	US-PGPUB;	14:13
		layer)	EPO; JPO;	
			DERWENT; IBM TDB	
			TDLI TDD	

-	8	(\$3minute or \$3min) near5 rate near5	USPAT;	2004/02/24
		(heat\$4) same (sic or silicon adj	US-PGPUB;	14:16
	1	carbide) near3 (film or layer)	EPO; JPO;	
	ļ		DERWENT;	
			IBM_TDB	
-	51		USPAT;	2004/02/24
		adj carbide) near3 (film or layer)	US-PGPUB;	14:31
			EPO; JPO;	
	4		DERWENT;	
	į .		IBM_TDB	
-	66	rate near3 (temperature) same (sic or	USPAT;	2004/02/24
Ì		silicon adj carbide) near3 (film or	US-PGPUB;	14:35
ļ		layer)	EPO; JPO;	
			DERWENT;	
	221		IBM_TDB	2004/02/24
	221	rapid near2 thermal same heat\$4 near2	USPAT;	2004/02/24
		rate	US-PGPUB;	14:36
			EPO; JPO;	
			DERWENT;	
	2	nonid noon? thousand noon boot 04 years?	IBM_TDB	2004/02/24
-	2	<u> </u>	USPAT;	2004/02/24
		rate same susceptor	US-PGPUB; EPO; JPO;	13.3/
			DERWENT;	
			IBM TDB	
_	24	rapid near2 thermal same heat\$4 near2	USPAT;	2004/02/24
	23	rate same product\$	US-PGPUB;	14:56
		Tace same producty	EPO; JPO;	11.50
	ļ		DERWENT;	
			IBM TDB	
-	31	rapid near2 thermal same heat\$4 near2	USPAT;	2004/02/24
		rate same (deposit\$ or grow\$3)	US-PGPUB;	15:29
		The Dame (deposits of growing)	EPO; JPO;	1 43.23
	1		DERWENT;	
	1	*	IBM TDB	
l –	77	rapid near2 thermal near20 (sic or	USPĀT;	2004/02/24
		silicon adj carbide)	US-PGPUB;	15:29
		-	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	31	rapid near2 thermal near20 (sic or	USPAT;	2004/02/24
		silicon adj carbide) near4 (layer or	US-PGPUB;	15:29
		film)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	00004/0=/==
-	<sup>67</sup>	(silicon or si) near2 substrate and (RTP	USPAT;	2004/03/01
		or rapid adj thermal near2 process\$5)	US-PGPUB;	15:46
		near3 rate	EPO; JPO;	
			DERWENT;	
_		laid or dilidon add cambid-1 16:1	IBM_TDB	2004/02/01
_	3	(sic or silicon adj carbide) near2 (film or layer) and (RTP or rapid adj thermal	USPAT;	2004/03/01
		near2 process\$5) near3 rate	US-PGPUB; EPO; JPO;	15:48
		Hearz processys) Hears race	DERWENT;	
			IBM TDB	
_	4	   (sic or silicon adj carbide) same (RTP or	USPAT;	2004/03/01
		rapid adj thermal near2 process\$5) near3	US-PGPUB;	15:48
		rate	EPO; JPO;	20.10
			DERWENT;	
			IBM TDB	
_	673	(sic or silicon adj carbide) same (heat\$3	USPAT;	2004/03/01
		or ramp\$4 or elevat\$4) near5 rate	US-PGPUB;	15:50
		,	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	50	(sic or silicon adj carbide) same (heat\$3	USPAT;	2004/03/01
		or ramp\$4 or elevat\$4) near5 rate near10	US-PGPUB;	15:53
		(rapid\$3 or fast\$3)	EPO; JPO;	
			DERWENT;	
	ľ		IBM_TDB	

<u> </u>	2	4855254.pn.	USPAT;	2004/03/01
			US-PGPUB;	16:00
			EPO; JPO;	Į.
İ			DERWENT;	
1			IBM_TDB	0004/02/01
_	2	reactor same rapid near2 thermal near10	USPAT;	2004/03/01
	i 1	rate same substrate	US-PGPUB;	16:01
	1		EPO; JPO;	
1			DERWENT;	
			IBM_TDB	2004/03/01
_	16	reactor same rapid near2 thermal near10	USPAT;	16:24
		rate	US-PGPUB;	10.24
			EPO; JPO;	
			DERWENT; IBM TDB	
	1	0.1	USPAT;	2004/03/01
-	23	tungsten near2 halogen near2 lamp near10	US-PGPUB;	16:26
	1	(rate)	EPO; JPO;	10.20
Į.			DERWENT;	
	1		IBM TDB	
1	1		TDL TDD	